



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	Package	I _D T _A = +25°C
60V	3Ω @ V _{GS} = 10V	SOT23	310mA
607	4Ω @ V _{GS} = 5V	30123	270mA

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

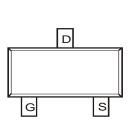
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating Matte Tin Finish Annealed over Alloy 42 Leadframe). (€3)
- Weight: 0.006 grams (Approximate)

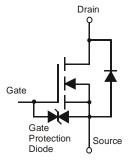




Top View



Top View Pin Configuration



Equivalent Circuit

Ordering Information (Note 5)

Part Number	Case	Packaging
DMN65D8LQ-7	SOT23	3,000/Tape & Reel
DMN65D8LQ-13	SOT23	10,000/Tape & Reel

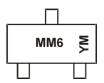
SOT23

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information



MM6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011) M = Month (ex: 9 = September)

Date Code Key

Year	2011		2015	2010	6 20°	17 20	018 2	2019	2020	2021	2022	2023
Code	Υ		С	D	Е		F	G	Н	ı	J	K
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	60	V		
Gate-Source Voltage	V_{GSS}	±20	V		
Continuous Drain Current (Note 7) V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	310 240	mA
Continuous Drain Current (Note 7) V _{GS} = 5V	I _D	270 210	mA		
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	800	mA		
Maximum Body Diode Continuous Current (Note 6)			Is	500	mA

Thermal Characteristics

Characteristic		Symbol	Value	Units	
Total Dower Discinstion	(Note 7)	5	370	mW	
Total Power Dissipation	(Note 6)	P_{D}	540		
Thermal Desistance, Junction to Ambient	(Note 7)	2	348		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	241	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	R ₀ JC	91		
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C	

Notes:

^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.

^{7.} Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.



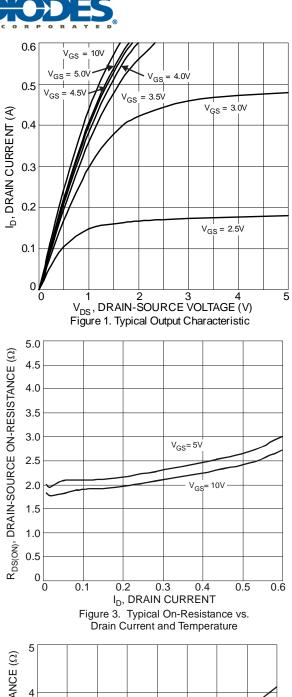
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

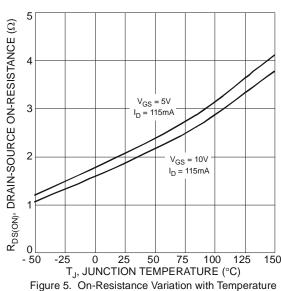
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	_		V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Body Leakage	I _{GSS}	_	_	±5	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	1.2	_	2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance		_	2	3	Ω	$V_{GS} = 10V, I_D = 0.115A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	2.5	4	Ω	$V_{GS} = 5V, I_D = 0.115A$
Forward Transconductance	g FS	80	290		mS	$V_{DS} = 10V, I_D = 0.115A$
Diode Forward Voltage	V_{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	_	22.0	_		
Output Capacitance	Coss	_	3.2		pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	C _{rss}	_	2.0	_		
Gate Resistance	R_{G}	_	79.9	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge V _{GS} = 10V	Qg	_	0.87	_		
Total Gate Charge V _{GS} = 4.5V	Q_{g}	_	0.43	_	nC	$V_{GS} = 10V, V_{DS} = 30V,$
Gate-Source Charge	Qgs	_	0.11	—	nc nc	$I_D = 150 \text{mA}$
Gate-Drain Charge	Q _{gd}	_	0.11	_		
Turn-On Delay Time	t _{D(on)}	_	2.7	—		
Turn-On Rise Time	t _r	_	2.8	_	nS	$V_{DD} = 30V$, $I_D = 0.115A$, $V_{GEN} = 10V$.
Turn-Off Delay Time	t _{D(off)}	_	12.6	_	110	$R_{GEN} = 25\Omega$
Turn-Off Fall Time	t _f	_	7.3	_		

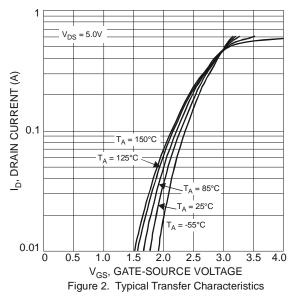
Notes:

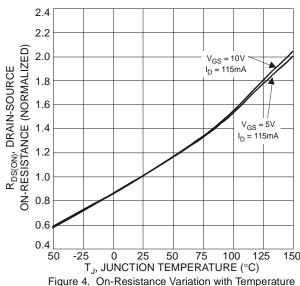
^{8.} Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to production testing.











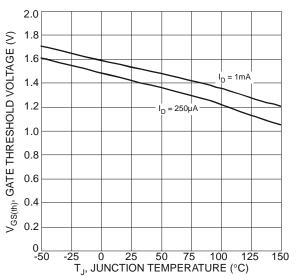
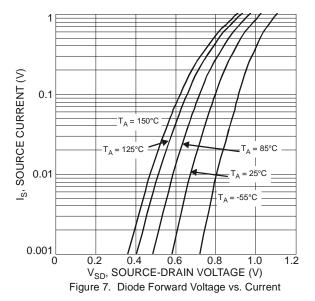


Figure 6. Gate Threshold Variation vs. Ambient Temperature





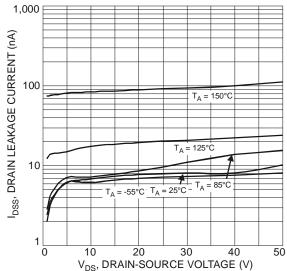
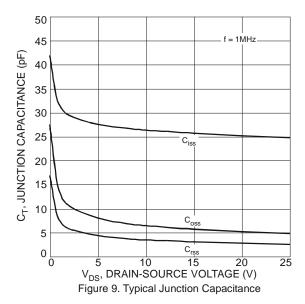
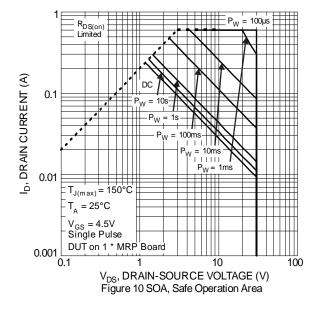
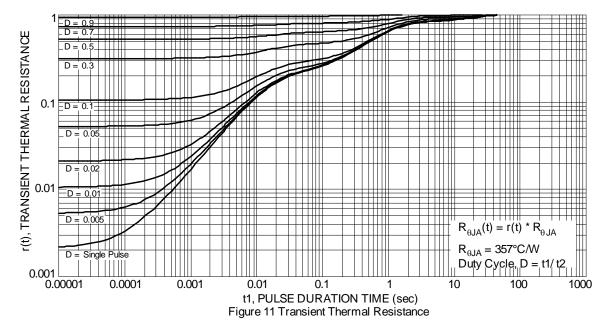


Figure 8. Typical Drain-Source Leakage Current vs. Voltage







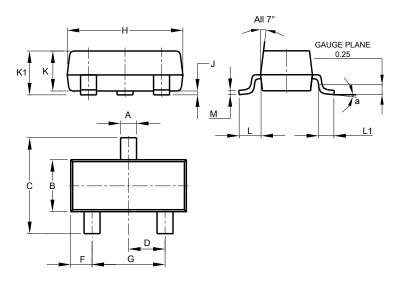




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

SOT23

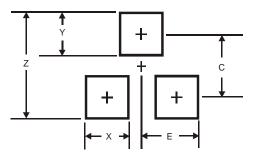


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а		8°					
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.





Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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